

1000MP

0.6 Watts, 18 Volts, Class A Linear to 1150 MHz

GENERAL DESCRIPTION

The 1000MP is a COMMON EMITTER transistor capable of providing 0.6 Watt of Class A, RF output power to 1150 MHz. This transistor is specifically designed for general Class A amplifier applications. It utilizes gold metalization and diffused ballasting to provide high reliability and supreme ruggedness.

CASE OUTLINE 55FW-2 (Common Emitter)

ABSOLUTE MAXIMUM RATINGS

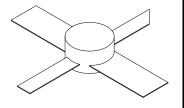
Maximum Power Dissipation

Device Dissipation @ 25°C 5.3 W

Maximum Voltage and Current

Maximum Temperatures

Storage Temperature $-40 \text{ to } +150 \text{ }^{\circ}\text{C}$ Operating Junction Temperature $+200 \text{ }^{\circ}\text{C}$



ELECTRICAL CHARACTERISTICS @ 25°C

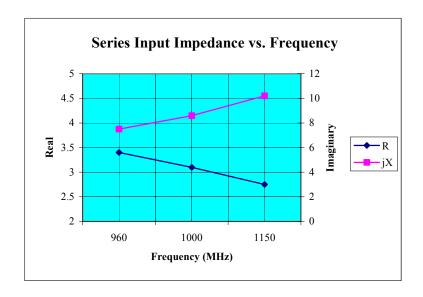
SYMBOL	CHARACTERISTICS	TEST CONDITIONS	MIN	TYP	MAX	UNITS
P _{OUT}	Power Output	F = 1000 MHz	0.6	0.8		W
P _{IN}	Power Input	$I_{\rm C} = 140 \; {\rm mA}$			0.05	W
P_{G}	Power Gain	$V_{\rm CC} = 18 \text{ Volts}$	10.8			dB
F_{T}	Transition Frequency		3.4	3.7		GHz
VSWR	Load Mismatch Tolerance				10:1	

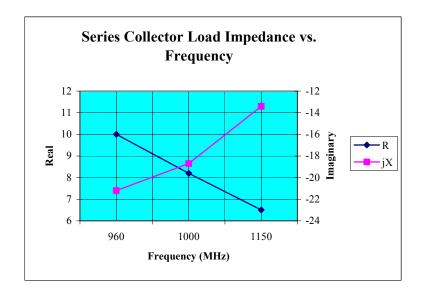
FUNCTIONAL CHARACTERISTICS @ 25°C

BV_{EBO}	Emitter to Base Breakdown	$I_E = 1 \text{mA}$	3.5			V
BV_{CBO}	Collector to Base Breakdown	$I_C = 1 \text{ mA}$	40			V
BV_{CER}	Collector to Emitter Breakdown	$I_{ER} = 5 \text{mA}, R_{BE} = 10$	22			V
I_{CES}	Collector Leakage Current	$V_{CE} = 28V$				
h_{FE}	DC – Current Gain	$V_{CE} = 5V$, $Ic = 100mA$	15		120	
C_{OB}	Capacitance	$V_{CB} = 28V$, $F = 1$ MHz		2.0	3.0	pF
$\theta_{\rm JC}^{-1}$	Thermal Resistance				33	°C/W

Note 1: At rated output power

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Frequency	Zin		Zcl		
(MHz)	R	jХ	R	jΧ	
960	3.4	7.5	10	-21.2	
1000	3.1	8.6	8.2	-18.7	
1150	2.75	10.2	6.5	-13.4	

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